

ABSTRACT OF THE DISCLOSURE

The plasma processing apparatus for providing plasma processing to an object 114 placed inside a processing chamber 104 comprises a vacuum chamber 104, a process gas feeder 105 feeding gas into chamber 104, a wafer electrode 115 disposed within chamber 114 for mounting the object 114, a wafer bias power generator 117 supplying bias voltage to electrode 115, and a plasma generating means 112 for generating plasma within chamber 104, wherein said wafer bias power generator includes a clip circuit for clipping either the positive-side voltage or negative-side voltage to a predetermined voltage.